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Electrical properties of thin films of a-GaxTe100-x composed of nanoparticles

(2011) *Philosophical Magazine Letters*, 91 (3), pp. 207-213.

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Abstract

Thin films of GaxTe100-x (x = 3, 6, 9 and 12) have been synthesized by thermal evaporation. From SEM images, it is observed that all the films contain nanoparticles of sizes varying from 100 to 200 nm. The dc electrical conductivity of the as-deposited films of GaxTe 100-x nanoparticles is measured as a function of temperature range from 298 to 383 K, and increases exponentially with temperature. The value of the activation energy, calculated from the slope of $\ln \sigma_{dc}$ versus $1000/T$ plots, is found to decrease with increase in the Ga content. On the basis of the value of the pre-exponential factor σ_0 , it is suggested that the conduction is due to thermally assisted tunneling of carriers in localized states near the band edges. The optical measurements suggest an indirect optical band gap in this system. The value of the optical band gap decreases on increasing the Ga concentration. © 2011 Taylor & Francis.

Author Keywords

a-GaxTe100-x nanoparticles; activation energy; dc conductivity; optical band gap; SEM; TEM; thin films; XRD

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